

*Subcl*

a reverse-tunneling layer over the first surface;  
a first transparent ohmic contact electrode  
positioned directly on the reverse-tunneling layer;  
and

5 a second transparent ohmic contact electrode  
positioned over the second surface.

*A' ant.*

2. (Amended) The light emitting diode of claim 1,  
wherein the insulating substrate comprises sapphire,  
10 and the first transparent ohmic contact electrode  
and the second transparent ohmic contact electrode  
comprise the same material.

3. (Amended) The light emitting diode of claim 1,  
15 wherein the first transparent ohmic contact  
electrode or the second transparent ohmic contact  
electrode comprises at least one selected from a  
group comprising indium tin oxide (ITO), cadmium tin  
oxide (CTO), and titanium-tungsten nitride (TiWN).

20 4. (Amended) A light emitting diode comprising:  
a substrate;  
a semiconductor stack positioned over the  
substrate;  
25 a reverse-tunneling layer over the semiconductor  
stack; and  
an ohmic contact electrode formed directly on the  
reverse-tunneling layer.

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30 8. (New) The light emitting diode of claim 4, wherein  
the ohmic contact electrode is a transparent ohmic  
contact electrode.

- 92  
enclosed
9. (New) The light emitting diode of claim 8, wherein the transparent ohmic contact electrode is a non-metal transparent ohmic contact electrode.
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